



P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
	155mΩ @ V _{GS} = -10V	-3.2A
-60V	240mΩ @ V _{GS} = -4.5V	-2.6A

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

https://www.diodes.com/products/automotive/automotive-

This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.

https://www.diodes.com/quality/product-definitions/

Description and Applications

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

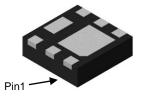
- **Battery Management Application**
- **Power Management Functions**
- **DC-DC Converters**

Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.007 grams (Approximate)

U-DFN2020-6 (Type F)



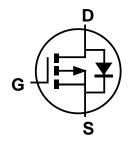


Bottom View

Top View

6 D D 1 D 5 D D S G

Pin Out **Bottom View**



Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging		
DMP6250SFDF-7	U-DFN2020-6 (Type F)	3,000/Tape & Reel		
DMP6250SFDF-13	U-DFN2020-6 (Type F)	10,000/Tape & Reel		

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information

Site 1:



5P = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Key

Year	2015		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	С		Н	I	J	K	L	М	N	0	Р	R
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Site 2:



5P = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 0 = 2020) W = Week (ex: a = week 27; z represents week 52 and 53)

X = Internal Code (ex: U = Monday)

Date Code Key

Year	2015		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	5		0	1	2	3	4	5	6	7	8	9
Week		1.	-26			27-	-52			5	3	
Code		A-Z			a-z				Z			
Internal Code	Sur	1	Mon		Tue	W	ed	Thu		Fri		Sat
Code	Т		U		V	V	٧	Х		Y		Z



Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	VDSS	-60	V		
Gate-Source Voltage	V _{GSS}	±20	V		
Continuous Drain Current (Note 6) V 40V	Steady State	T _A = +25°C T _A = +70°C	lo	-3.2 -2.2	А
Continuous Drain Current (Note 6) V _{GS} = -10V	lo	-3.8 -2.7	А		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	-12	А
Continuous Source-Drain Diode Current (Note 6)	Is	-2	Α		
Avalanche Current (Note 7) L = 0.1mH	las	-12	A		
Avalanche Energy (Note 7) L = 0.1mH			Eas	8	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Total Power Dissipation (Note 5)	T _A = +25°C	D-	0.8	W	
Total Power Dissipation (Note 5)	$T_A = +70^{\circ}C$	PD	0.5	VV	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Reja	156	°C/W	
Thermal Resistance, Junction to Ambient (Note 3)	t<10s	Көја	121	C/VV	
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$	Pp	2.0	W	
Total Power Dissipation (Note 6)	$T_A = +70$ °C	PD	1.3	VV	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Reja	63	°C/W	
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	Көја	43	C/VV	
Thermal Resistance, Junction to Case	Steady State	Rejc	7.6	°C/W	
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C	

5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

7. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.

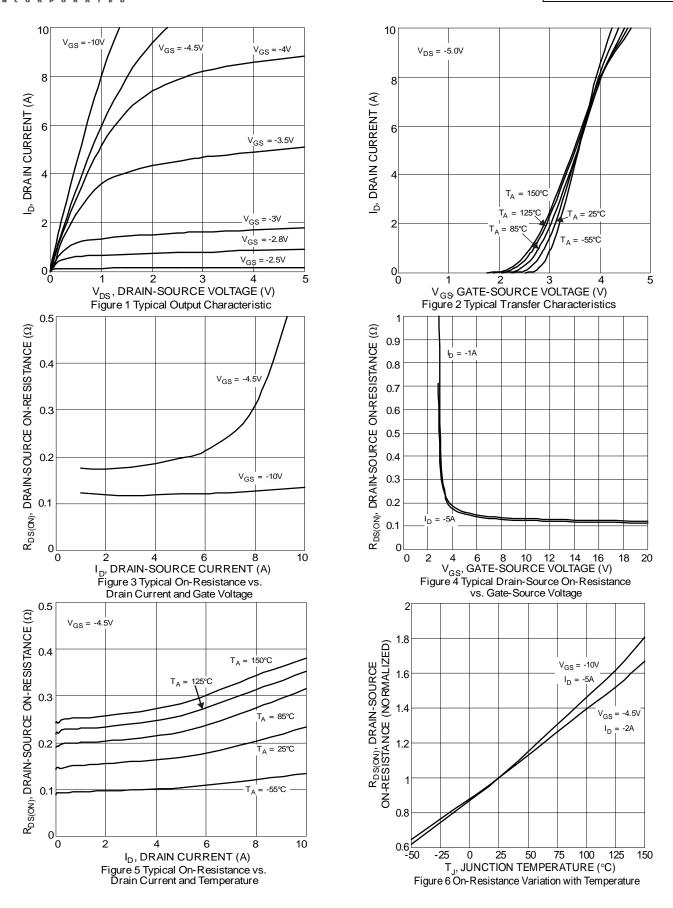
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-60	_	_	V	$V_{GS} = 0V, I_{D} = -250\mu A$
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	-1	μΑ	$V_{DS} = -60V, V_{GS} = 0V$
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 16V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	Vgs(th)	-1	_	-3	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$
Static Drain-Source On-Resistance	Descent		_	155	mΩ	$V_{GS} = -10V, I_{D} = -2A$
Static Dialit-Source Off-Nesistance	RDS(ON)	_	_	240	11122	$V_{GS} = -4.5V, I_{D} = -1A$
Diode Forward Voltage	VsD	_	-0.7	-1.2	V	$V_{GS} = 0V$, $I_{S} = -2A$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	Ciss	_	612	_	pF	V 20V V 0V
Output Capacitance	Coss	_	36	_	pF	V _{DS} = -20V, V _{GS} = 0V, - f = 1MHz
Reverse Transfer Capacitance	C _{rss}	_	26		pF	1 – 11011 12
Gate Resistance	Rg	_	13	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge (V _{GS} = -10V)	Q _G	_	8.9	_	nC	
Total Gate Charge (V _{GS} = -4.5V)	Q_{G}	_	4.3		nC	Vps = -30V. lp = -2A
Gate-Source Charge	Qgs	_	1.4	_	nC	VDS = -30 V, ID = -2A
Gate-Drain Charge	Q_{GD}	_	1.7	_	nC	
Turn-On Delay Time	td(on)	_	7.6	_	ns	
Turn-On Rise Time	tR	_	11.6	_	ns	$V_{GS} = -10V, V_{DS} = -30V,$
Turn-Off Delay Time	tD(OFF)	_	79.8	_	ns	$R_G = 50\Omega$, $I_D = -1A$
Turn-Off Fall Time	tF	_	37.8	_	ns	
Reverse Recovery Time	t _{RR}	_	10.8	_	ns	I _S = -1A, di/dt = 100A/µs
Reverse Recovery Charge	Qrr	_	3.8	_	nC	$I_S = -1A$, $di/dt = 100A/\mu s$

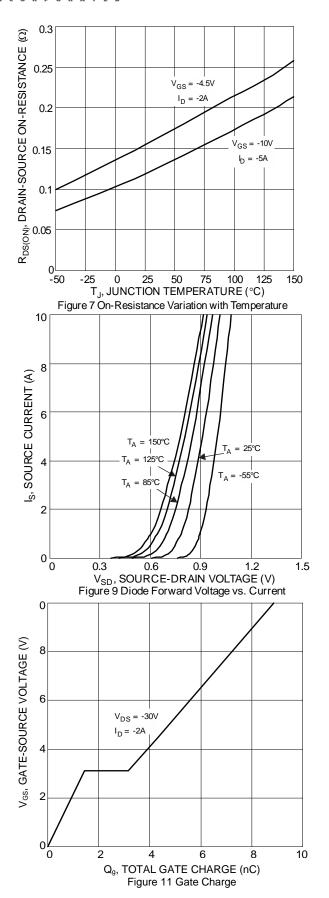
8. Short duration pulse test used to minimize self-heating effect. Notes:

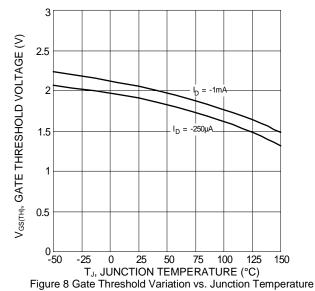
9. Guaranteed by design. Not subject to product testing.











10000 f=1MHz C_T, JUNCTION CAPACITANCE (pF) 100 10 _

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 $V_{\rm DS}$, DRAIN-SOURCE VOLTAGE (V) Figure 10 Typical Junction Capacitance

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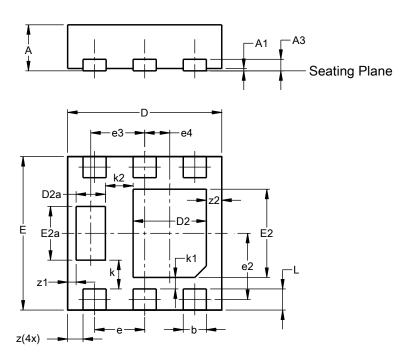
30



Package Outline Dimension

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)

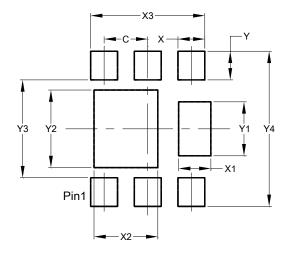


U-DFN2020-6						
	(Тур	oe F)				
Dim	Min	Max	Тур			
Α	0.57	0.63	0.60			
A1	0.00	0.05	0.03			
A3	-					
b	0.25	0.35	0.30			
D	1.95	2.05	2.00			
D2	0.85	1.05	0.95			
D2a	0.33	0.43	0.38			
Е	1.95	2.05	2.00			
E2	1.05	1.25	1.15			
E2a	0.65	0.75	0.70			
е		0.65 BS	_			
e2	C).863 BS	SC			
е3		0.70 BS	С			
e4	C).325 BS	SC			
k		0.37 BS	С			
k1		0.15 BS	С			
k2	0.36 BSC					
L	0.225 0.325 0.275					
Z		0.20 BS				
z 1).110 BS	_			
z2		0.20 BS	С			
All C	imens	ions in	mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)



Dimensions	Value (in mm)				
С	0.650				
X	0.400				
X1	0.480				
X2	0.950				
Х3	1.700				
Y	0.425				
Y1	0.800				
Y2	1.150				
Y3	1.450				
Y4	2.300				



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